



DB4

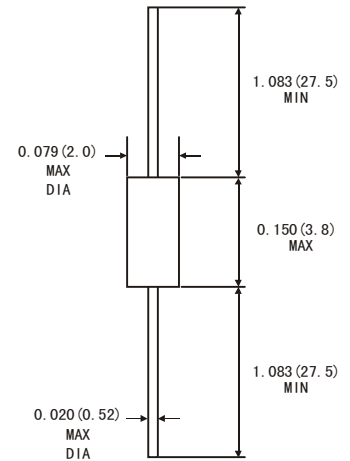
SILICON BIDIRECTIONAL DIAC

FEATURES

The three layer, two terminal, axial lead, hermetically sealed diacs are designed specifically for triggering thyristors. They demonstrate low breakover current at breakover voltage as they withstand peak pulse current, The breakover symmetry is within three volts. These diacs are intended for use in thyristors phase control , circuits for lamp dimming, universal motor speed control ,and heat control.

DB4 are bi-directional triggered diode designed to operate in conjunction with Triacs and SCR's

DO-35(GLASS)



Dimensions in inches and (millimeters)

ABSOLUTE RATINGS(LIMITING VALUES)

Symbols	Parameters		Value				Units
			DB4				
PC	Power Dissipation on Printed Circuit(L=10mm)	T _A =50°C	150				mW
I _{TRM}	Repetitive Peak on-state Current	t _p =10μs F=100Hz	2.0	2.0	2.0	16	A
T _{STG} /T _J	Storage and Operating Junction Temperature		-40 to +125/-40 to 110				°C

ELECTRICAL CHARACTERISTICS

Symbols	Parameters	Test Conditions	Value				Units
			DB4				
V _{BO}	Breakover Voltage (Note 2)	C=22nF(Note 2) See diagram 1	Min	35			V
			Typ	40			
			Max	45			
$\frac{ +V_{BO} }{ -V_{BO} }$	Breakover Voltage Symmetry	C=22nF(Note 2) See diagram 1	Max	±3		-	V
$ \pm \Delta V $	Dynamic Breakover Voltage (Note1)	$\Delta I = (I_{BO} \text{ to } I_F = 10\text{mA})$ See Diagram 1	Min	5			V
V _O	Output Voltage (Note 1)	See Diagram 2	Min	5			V
I _{BO}	Breakover Current (Note1)	C=22nF(Note 2)	Max	100			μA
t _r	Rise Time (Note1)	See Diagram 3	Typ	1.5			μS
I _B	Leakage Current (Note1)	V _B =0.5 V _{BO} max see diagram 1	Max	10			μA

Notes: 1.Electrical characteristics applicable in both forward and reverse directions.
2.Connected in parallel with the devices.